## METHOD OF AND APPARATUS FOR CONTROLLING THE CHEMICAL MECHANICAL POLISHING OF MULTILE LAYERS ON A SUBSTRATE

Application No. 10/726,650 – Attorney Docket No. SEC.1082 Inventors: Dea-Yun Kim et al.



Fig. 1

(PRIOR ART)

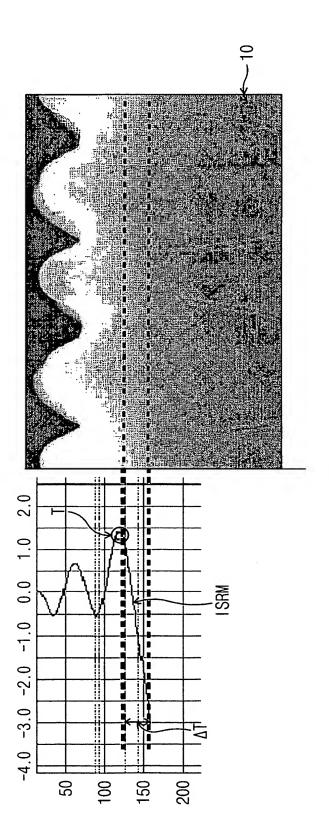
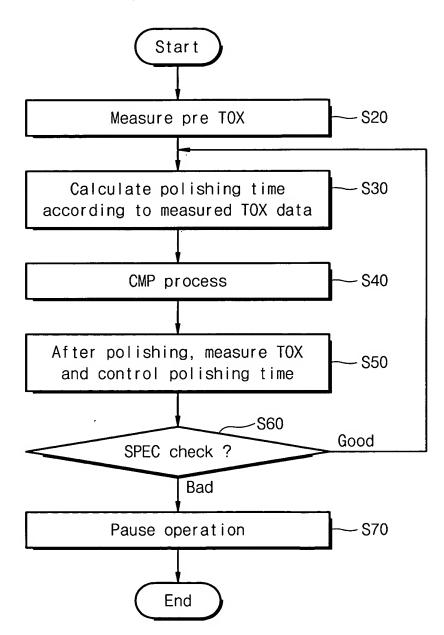


Fig. 2

(PRIOR ART)



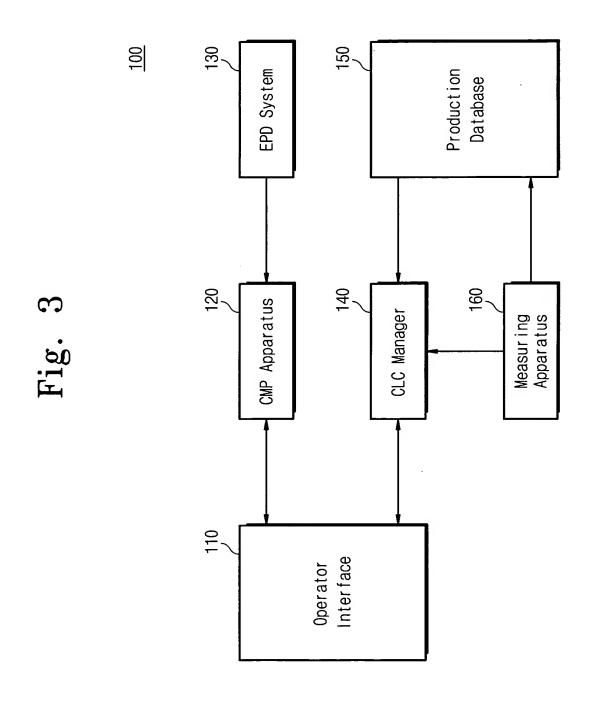
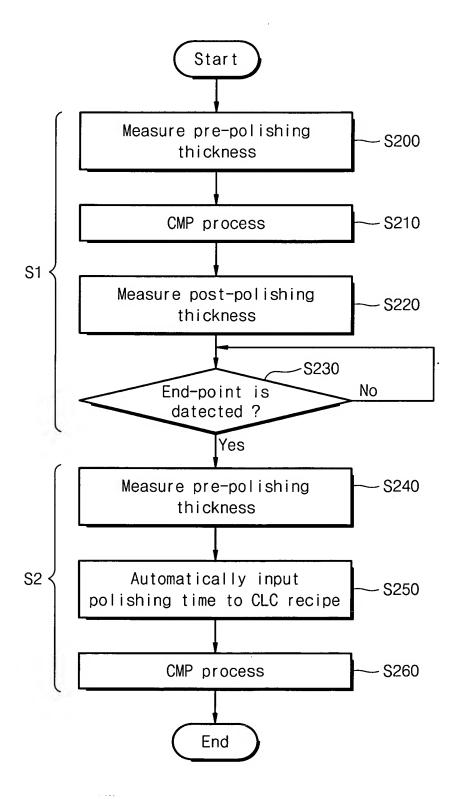


Fig. 4



## METHOD OF AND APPARATUS FOR CONTROLLING THE CHEMICAL MECHANICAL POLISHING OF MULTILE LAYERS ON A SUBSTRATE Application No. 10/726,650 – Attorney Docket No. SEC.1082 Inventors: Dea-Yun Kim et al.

## Fig. 5

	300
310	320
☐ Main polish Step ✓	☑ Main polish Step ✓
Step 2: Applying Endpoint	Step 3: CLC Time Control
Angular Accel/ Velocity Decel	Angular Accel/ Velocity Decel
Platen: rpm rpm/s	Platen: rpm rpm/s
Head: rpm rpm/s	Head: rpm rpm/s
Sweep: 5.0 sweeps/min From 5.05 in to 5.53 in Use 5 total zones Previous Sweep Configure Sweep	Sweep:  5.0 sweeps/min From 5.05 in to 5.53 in Use 5 total zones Previous Sweep  Configure Sweep
Over Ride Internal Tube: psi Ret Pressure psi Membrane: Pressure psi High Pressure Rinse  Deliv 1: Slurry min	Over Ride Internal Tube: Pressure  psi Ret Pressure  psi Membrane: Pressure  psi High Pressure Rinse  Deliv 1: Slurry  mi/ min
Deliv 2: No Slurry  By Endpoint Max Time: 60.0 s	Deliv 2: No Slurry  By Time/EP  Max Time: 20.0 s
312	322